

FK8V03060L

Silicon N-channel MOS FET

For lithium-ion secondary battery protection circuit

For DC-DC Converter

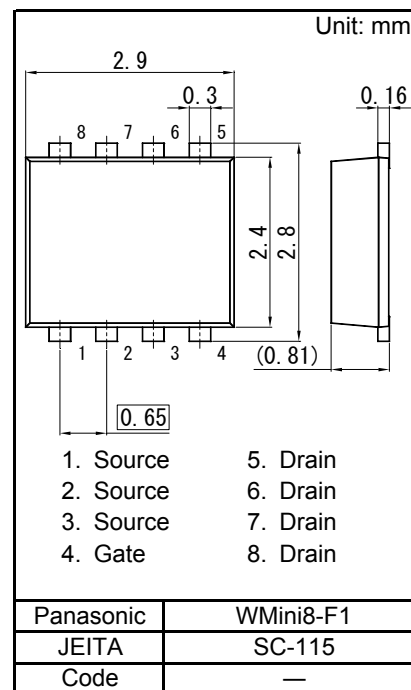
■ Features

- Low drain-source On-state Resistance
RDS(on) typ. = 22 mΩ (VGS = 4.5 V)
- High-speed switching : Qg = 3.8 nC
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 3F

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)



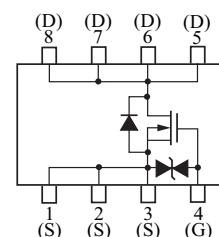
■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-source Voltage	VDS	33	V
Gate-source Voltage	VGS	±20	V
Drain Current (Steady State) ^{*1}	ID	6.5	A
Drain Current (t = 10 s) ^{*1}		8	
Drain Current (Pulsed) ^{*1,*2}		26	
Source Current (Pulsed) (Body Diode) ^{*1,*2}	ISp (BD)	6.5	
Total Power Dissipation (Steady State) ^{*1}	PD	1	W
Total Power Dissipation (t = 10 s) ^{*1}		1.5	
Channel Temperature	Tch	150	°C
Operating Ambient Temperature	Topr	-40 to +85	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Note) ^{*1} Device mounted on a glass-epoxy board (See Figure 1)

^{*2} Pulse test: Ensure that the channel temperature does not exceed 150°C

Internal Connection



Pin Name

- | | |
|-----------|----------|
| 1. Source | 5. Drain |
| 2. Source | 6. Drain |
| 3. Source | 7. Drain |
| 4. Gate | 8. Drain |

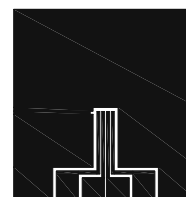


Figure1 FR4 Glass-Epoxy Board
25.4 mm × 25.4 mm × 0.8 mm

■ Electrical Characteristics Ta = 25°C ± 3°C

Static Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	33			V
Zero Gate Voltage Drain Current	IDSS	VDS = 33 V, VGS = 0 V			10	μA
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μA
Gate-source Threshold Voltage	Vth	ID = 0.48 mA, VDS = 10 V	1		2.5	V
Drain-source On-state Resistance *1	RDS(on)1	ID = 3.3 A, VGS = 10 V		15	20	mΩ
	RDS(on)2	ID = 3.3 A, VGS = 4.5 V		22	35	

Dynamic Characteristics

Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V f = 1 MHz		360		pF
Output Capacitance	Coss			70		
Reverse Transfer Capacitance	Crss			50		
Turn-on Delay Time *2	td(on)	VDD = 15 V, VGS = 0 to 10 V ID = 3.3 A		8		ns
Rise Time *2	tr			3		
Turn-off Delay Time *2	td(off)	VDD = 15 V, VGS = 10 to 0 V ID = 3.3 A		24		
Fall Time *2	tf			9		
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V, ID = 6.5 A		3.8		nC
Gate-source Charge	Qgs			1.4		
Gate-drain Charge	Qgd			1.6		

Body Diode Characteristic

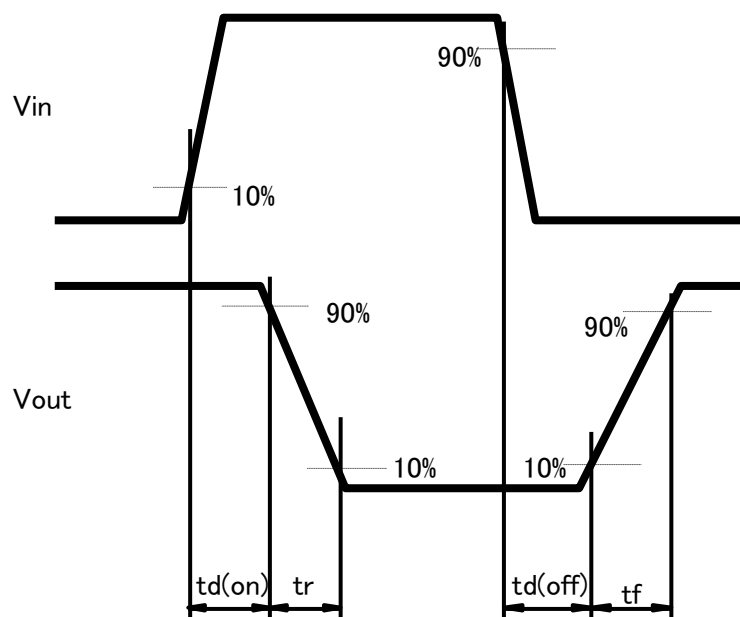
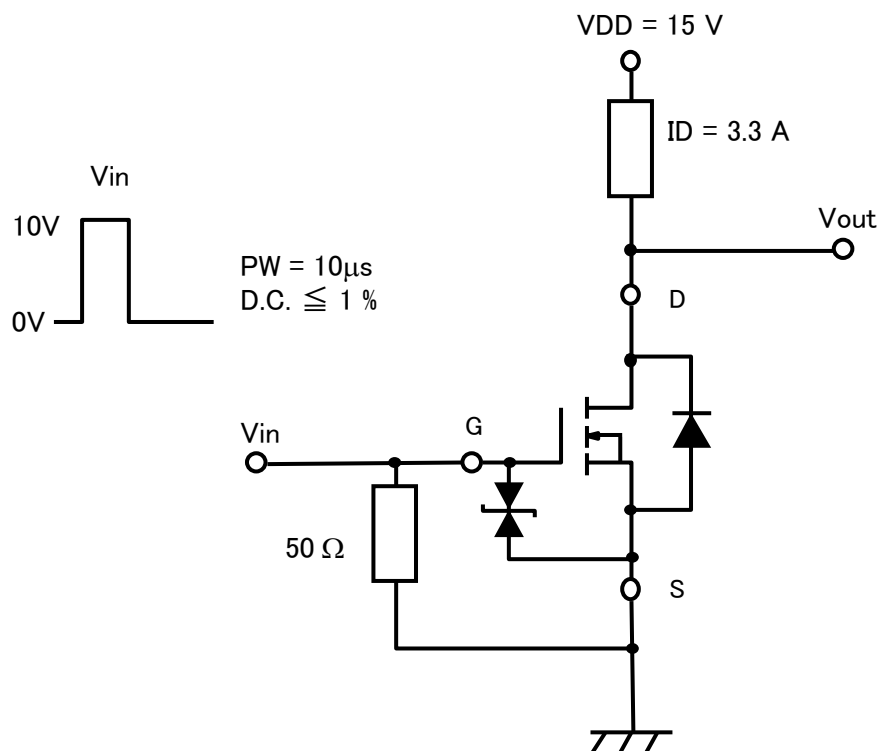
Diode Forward Voltage *1	VSD	IS = 3.3 A, VGS = 0 V		0.8	1.2	V
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Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

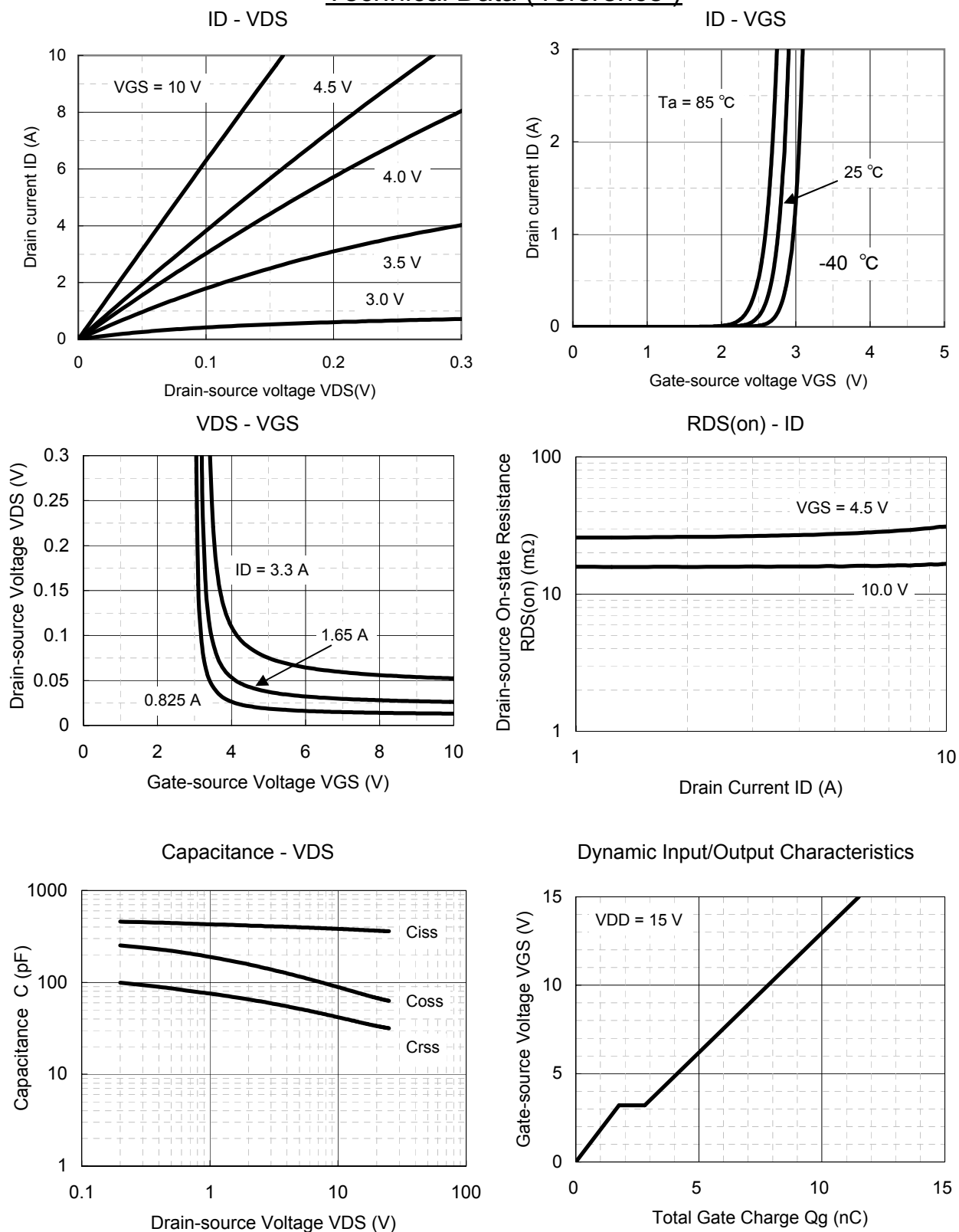
2. *1 Pulse test: Ensure that the channel temperature does not exceed 150°C

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

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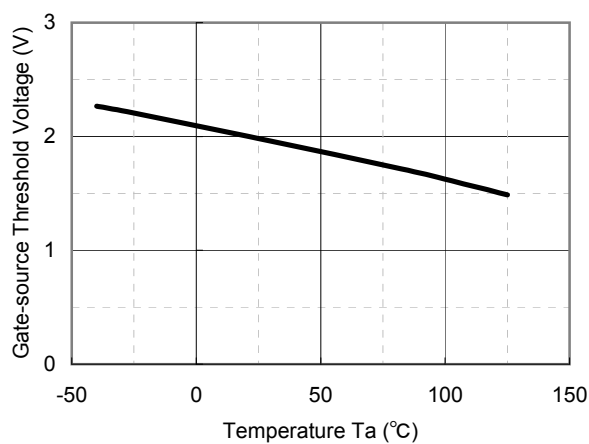


Technical Data (reference)

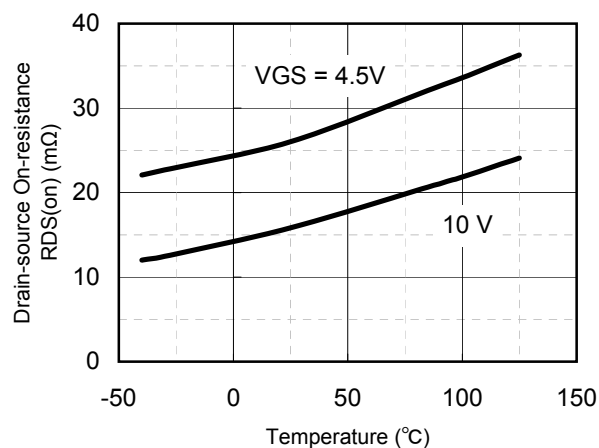


Technical Data (reference)

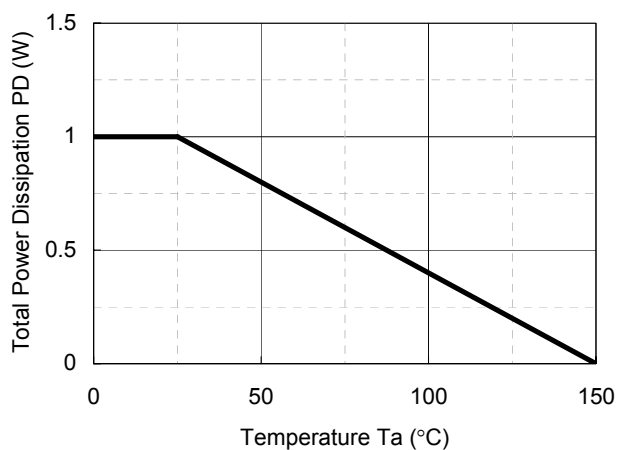
V_{th} - T_a



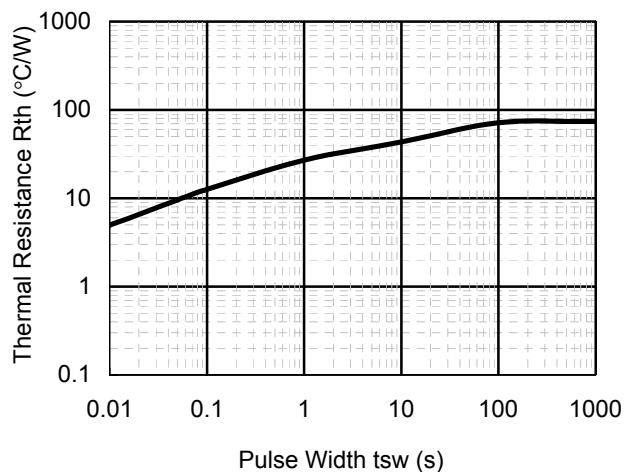
R_{DS(on)} - T_a



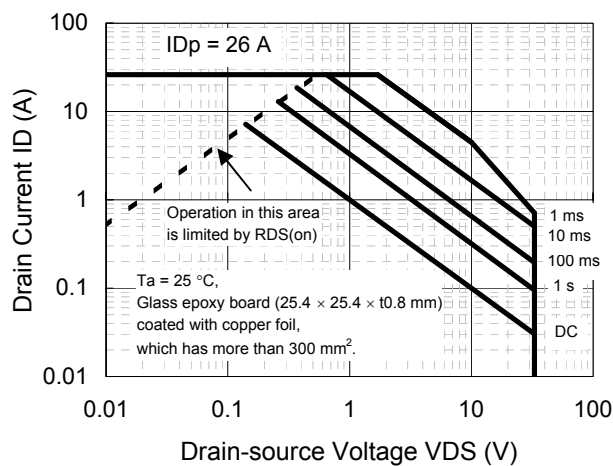
P_D - T_a



R_{th} - t_{sw}

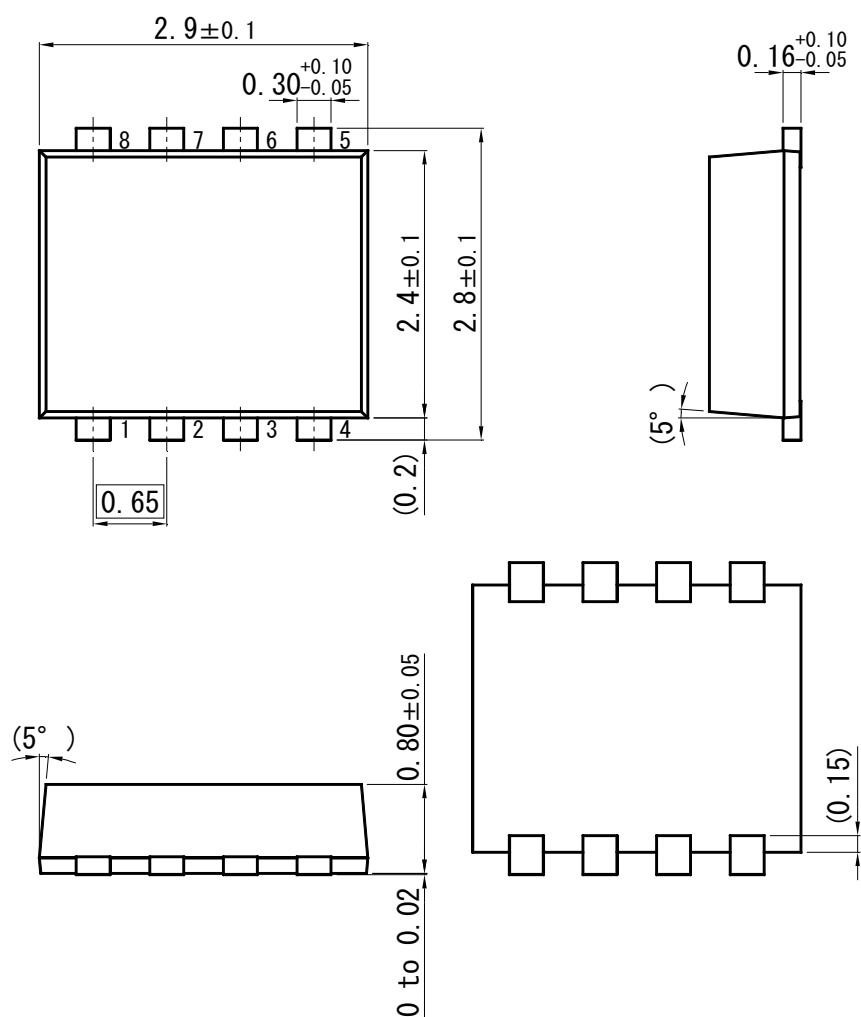


Safe Operating Area

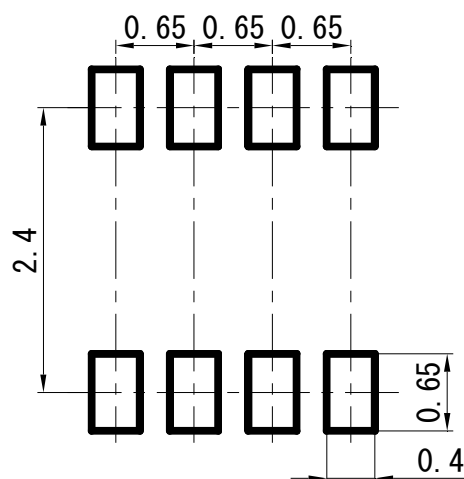


WMini8-F1

Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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